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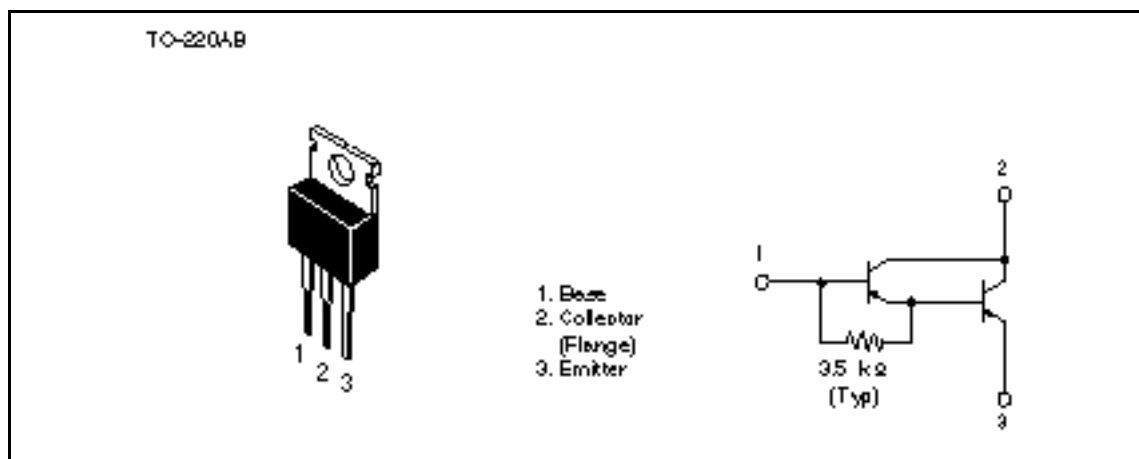
Silicon PNP Triple Diffused

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Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-60	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-8	A
Collector peak current	$I_{C(\text{peak})}$	-12	A
Collector power dissipation	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

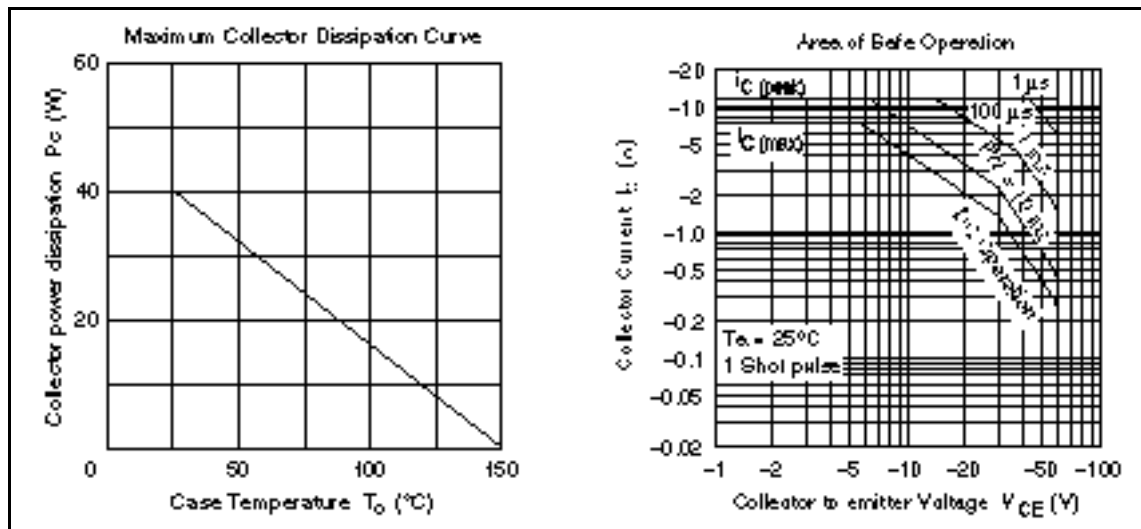
Note: 1. Value at $T_C = 25^\circ\text{C}$.

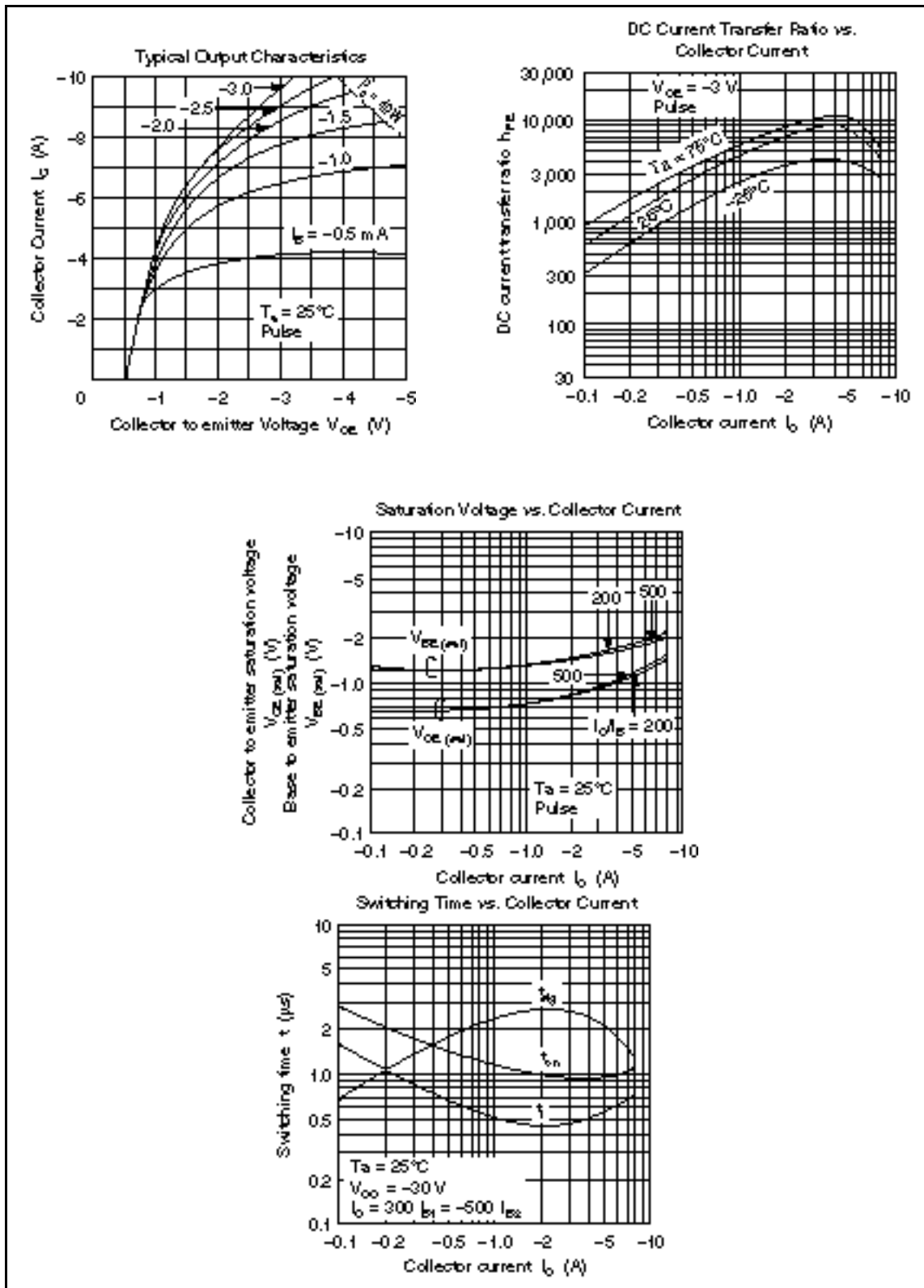
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Electrical Characteristics (Ta = 25°C)

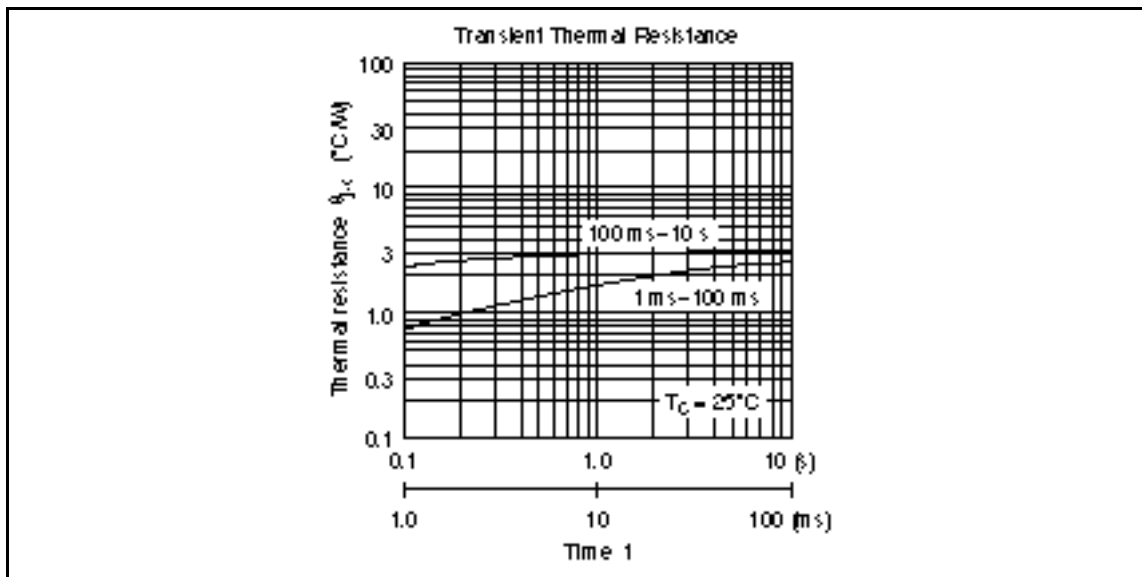
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -25 \text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -60 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-10	μA	$V_{CE} = -50 \text{ V}$, $R_{BE} =$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3 \text{ V}$, $I_C = -4 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-1.5	V	$I_C = -4 \text{ A}$, $I_B = -8 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	-3.0	V	$I_C = -8 \text{ A}$, $I_B = -80 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.0	V	$I_C = -4 \text{ A}$, $I_B = -8 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	-3.5	V	$I_C = -8 \text{ A}$, $I_B = -80 \text{ mA}^{*1}$
Turn on time	t_{on}	—	1.0	—	μs	$I_C = -4 \text{ A}$, $I_{B1} = -I_{B2} = -8 \text{ mA}$
Storage time	t_{stg}	—	2.5	—	μs	
Fall time	t_f	—	0.5	—	μs	

Note: 1. Pulse Test.





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